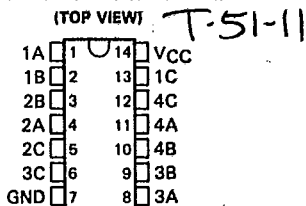


SN54HC4066, TLC4066I
SILICON-GATE CMOS QUADRUPLE BILATERAL ANALOG SWITCH

D2922, JANUARY 1986

- High Degree of Linearity
- High On-Off Output Voltage Ratio
- Low Crosstalk Between Switches
- Low On-State Impedance . . .Typically 30 Ohms at V_{CC} = 12 V
- Individual Switch Controls
- Extremely Low Input Current
- Functionally Interchangeable with National Semiconductor MM54/74HC4066, Motorola MC54/74HC4066, and RCA CD4066A

SN54HC4066 . . . J OR N PACKAGE
 TLC4066I . . . D OR N PACKAGE



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HC MOS Devices

description

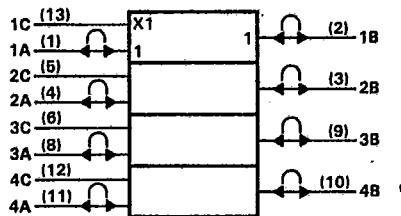
The TLC4066 is a silicon-gate CMOS quadruple analog switch integrated circuit designed to handle both analog and digital signals. Each switch permits signals with amplitudes up to 12 volts peak to be transmitted in either direction.

Each switch section has its own enable input control. A high-level voltage applied to this control terminal turns on the associated switch section.

Applications include signal gating, chopping, modulation or demodulation (modem), and signal multiplexing for analog-to-digital and digital-to-analog conversion systems.

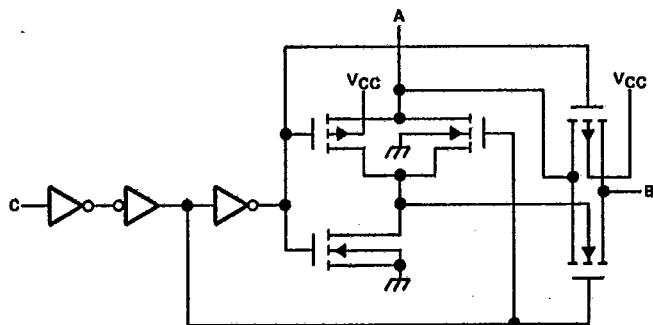
The SN54HC4066 is characterized for operation from -55°C to 125°C, and the TLC4066I is characterized from -40°C to 85°C.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



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SN54HC4066, TLC4066I
SILICON-GATE CMOS QUADRUPLE BILATERAL ANALOG SWITCH

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage range (see Note 1)	-0.5 V to 15 V
Control-input diode current ($V_I < 0$ or $V_I > V_{CC}$)	± 20 mA
I/O port diode current ($V_I < 0$ or $V_I/O < V_{CC}$)	± 20 mA
On-state switch current ($V_I/O = 0$ to V_{CC})	± 25 mA
Continuous current through V_{CC} or GND pins	± 50 mA
Continuous total dissipation at (or below) 25°C free-air temperature (see Note 2):	
D package	950 mW
J package	1025 mW
N package	875 mW
Operating free-air temperature, T_A : SN54HC4066	-55°C to 125°C
TLC4066I	-40°C to 85°C
Storage temperature range	-65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: D and N packages	260°C
Lead temperature 1,6 mm (1/16 inch) from case for 60 seconds: J package	300°C

- NOTES: 1. All voltages are with respect to ground unless otherwise specified.
 2. For operation above 25°C free-air temperature, see Dissipation Derating Table.

DISSIPATION DERATING TABLE

Package	Maximum Power Dissipation			Derating Factor
	25°C	85°C	125°C	
D	950 mW	494 mW		7.6 mW/°C
J	1025 mW	533 mW	205 mW	8.2 mW/°C
N	875 mW	455 mW	175 mW	7.0 mW/°C

recommended operating conditions

	MIN	NOM	MAX	UNIT
Supply voltage, V_{CC}	2 [†]	5	12	V
I/O port voltage, V_I/O	0		V_{CC}	V
High-level input voltage, V_{IH}	$V_{CC} = 2$ V	1.5	V_{CC}	V
	$V_{CC} = 4.5$ V	3.15	V_{CC}	
	$V_{CC} = 9$ V	6.3	V_{CC}	
	$V_{CC} = 12$ V	8.4	V_{CC}	
Low-level input voltage, V_{IL}	$V_{CC} = 2$ V	0	0.3	V
	$V_{CC} = 4.5$ V	0	0.9	
	$V_{CC} = 9$ V	0	1.8	
	$V_{CC} = 12$ V	0	2.4	
Input rise time, t_r	$V_{CC} = 2$ V		1000	ns
	$V_{CC} = 4.5$ V		500	
	$V_{CC} = 9$ V		400	
Input fall time, t_f	$V_{CC} = 2$ V		1000	ns
	$V_{CC} = 4.5$ V		500	
	$V_{CC} = 9$ V		400	
Operating free-air temperature, T_A	SN54HC4066	-55	125	°C
	TLC4066I	-40	85	

[†]With supply voltages at or near 2 volts, the analog switch on-state resistance becomes very nonlinear. It is recommended that only digital signals be transmitted at these low supply voltages.

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SN54HC4066, TLC4066I
SILICON-GATE CMOS QUADRUPLE BILATERAL ANALOG SWITCH

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	SN54HC4066			TLC4066I			UNIT
			MIN	TYP†	MAX	MIN	TYP†	MAX	
r _{SON} On-state switch resistance	I _S = 1 mA, V _A = 0 to V _{CC} , See Figure 1	4.5 V		100	220		100	200	Ω
		9 V		50	110		50	105	
		12 V		30	90		30	85	
	I _S = 1 mA, V _A = 0 or V _{CC} , See Figure 1	2 V		120	240		120	215	
		4.5 V		50	120		50	100	
		9 V		35	80		35	75	
On-state switch resistance matching	V _A = 0 to V _{CC} , See Figure 1	4.5 V		10	20		10	20	Ω
		9 V		5	15		5	15	
		12 V		5	15		5	15	
I _I Control input current	V _I = 0 or V _{CC}	2 V or 6 V			±1			±1	μA
I _{SOFF} Off-state switch leakage current	V _S = ±V _{CC} , See Figure 2	5.5 V		±10	±600		±10	±600	nA
		9 V		±15	±800		±15	±800	
		12 V		±20	±1000		±20	±1000	
I _{SON} On-state switch leakage current	V _A = 0 or V _{CC} , See Figure 3	5.5 V		±10	±150		±10	±150	nA
		9 V		±15	±200		±15	±200	
		12 V		±20	±300		±20	±300	
I _{CC} Supply current	V _I = 0 or V _{CC} , I _O = 0	5.5 V		2	40		2	20	μA
		9 V		8	160		8	80	
		12 V		16	320		16	160	
C _i Input capacitance	A or B	2 V to		15			15	pF	
	C	12 V		5	10		5		10
C _f Feedthrough capacitance	A to B	2 V to		5			5	pF	
		12 V							

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†All typical values are at T_A = 25°C.

SN54HC4086, TLC4086I
SILICON-GATE CMOS QUADRUPLE BILATERAL ANALOG SWITCH

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switching characteristics over recommended operating free-air temperature range, $C_L = 50$ pF (unless otherwise noted)

PARAMETER	TEST CONDITIONS	VCC	SN54HC4086			TLC4086I			UNIT
			MIN	TYP†	MAX	MIN	TYP†	MAX	
t_{pd} Propagation delay time, A to B or B to A	See Figure 4	2 V		25	75		15	30	ns
		4.5 V		5	15		5	13	
		9 V		4	12		4	10	
		12 V		3	13		3	11	
t_{on} Switch turn-on time	$R_L = 1$ k Ω , See Figures 5 and 6	2 V		32	160		32	125	ns
		4.5 V		8	30		8	25	
		9 V		6	18		6	16	
		12 V		5	15		5	13	
t_{off} Switch turn-off time	$R_L = 1$ k Ω , See Figures 5 and 6	2 V		45	252		45	210	ns
		4.5 V		15	54		15	45	
		9 V		10	48		10	40	
		12 V		8	45		8	38	
f_{co} Switch cutoff frequency (channel loss = 3 dB)		4.5 V		100		100		MHz	
		9 V		120		120			
$V_{OCF(PP)}$ Control feedthrough voltage to any switch, peak to peak	See Figure 7	4.5 V		180			180	mV	
Frequency at which crosstalk attenuation between any two switches equals 50 dB	See Figure 8	4.5 V		1			1	MHz	

†All typical values are at $T_A = 25^\circ\text{C}$.

PARAMETER MEASUREMENT INFORMATION

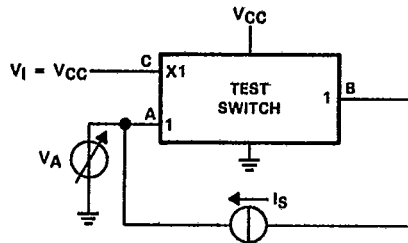
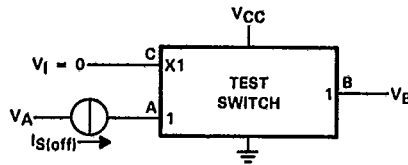


FIGURE 1. ON-STATE RESISTANCE TEST CIRCUIT



$V_S = V_A - V_B$
 CONDITION 1: $V_A = 0, V_B = V_{CC}$
 CONDITION 2: $V_A = V_{CC}, V_B = 0$

FIGURE 2. OFF-STATE SWITCH LEAKAGE CURRENT TEST CIRCUIT

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SN54HC4066, TLC4066I
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PARAMETER MEASUREMENT INFORMATION

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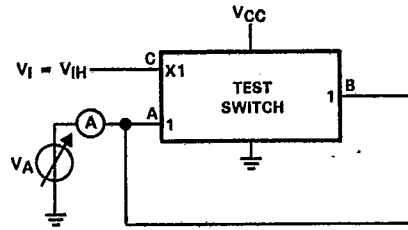


FIGURE 3. ON-STATE SWITCH LEAKAGE CURRENT TEST CIRCUIT

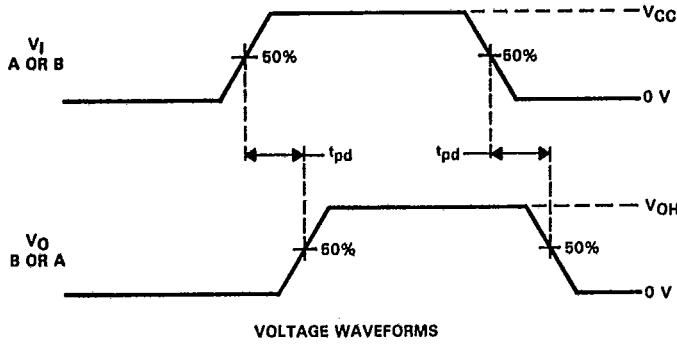
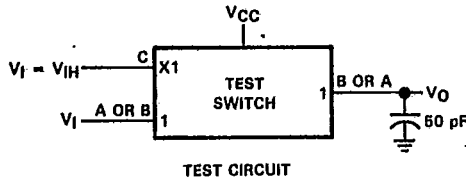


FIGURE 4. PROPAGATION DELAY TIME, SIGNAL INPUT TO SIGNAL OUTPUT

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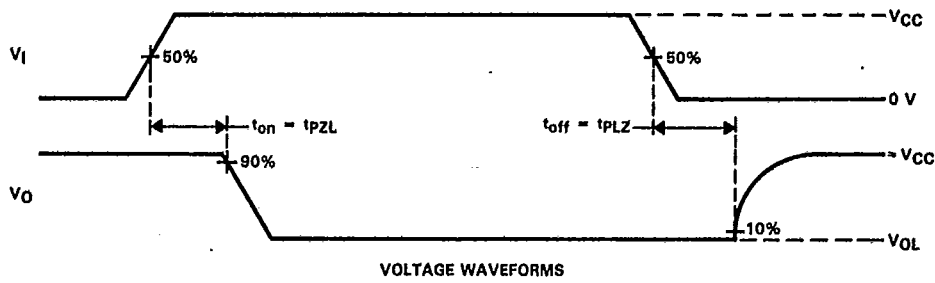
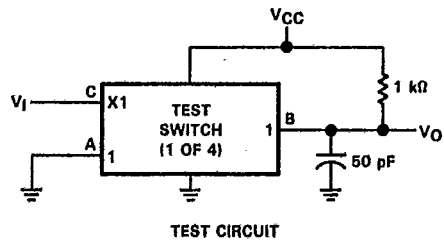


FIGURE 5. SWITCHING TIME (t_{pZL} , t_{PLZ}), CONTROL TO SIGNAL OUTPUT

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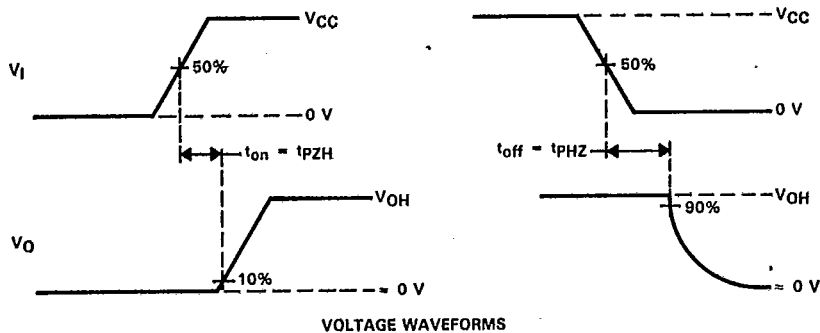
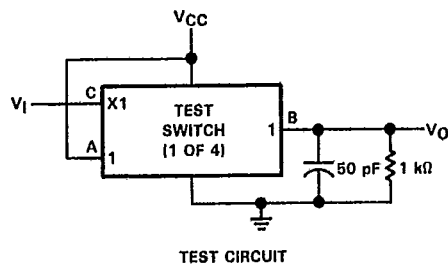


FIGURE 6. SWITCHING TIME (t_{pZH} , t_{pHZ}), CONTROL TO SIGNAL OUTPUT

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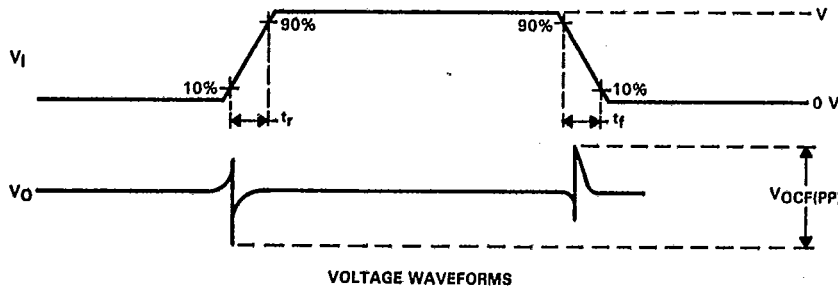
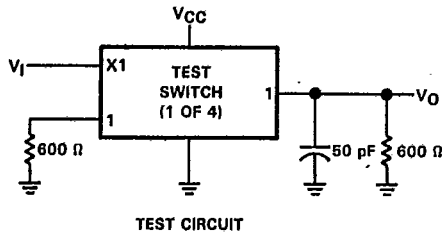
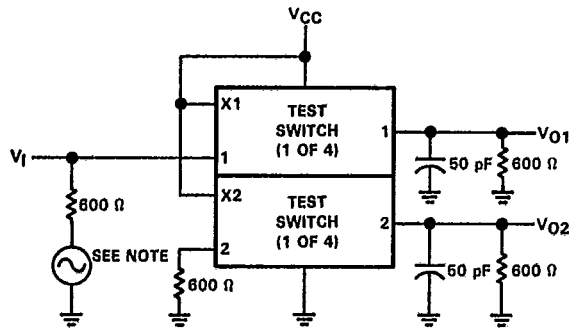


FIGURE 7. CONTROL FEEDTHROUGH VOLTAGE



NOTE: ADJUST f for $a_X = \frac{V_{O2}}{V_{O1}} = 50 \text{ dB}$.

FIGURE 8. CROSSTALK BETWEEN ANY TWO SWITCHES, TEST CIRCUIT

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